



PATENT
1592-0131P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Shigeto FUJIMURA et al. Conf.: 1881

Appl. No.: 09/753,662 Group: 1765

Filed: January 4, 2001 Examiner: M.A. Anderson

For: PROCESS FOR PRODUCING COMPOUND
SEMICONDUCTOR SINGLE CRYSTAL

REPLY UNDER 37 C.F.R. § 1.111

Assistant Commissioner for Patents
Washington, DC 20231

June 27, 2002

RECEIVED
JUN 27 2002
TECHNOLOGY CENTER 1700

Sir:

In reply to the Examiner's Office Action dated April 30, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS

Please amend claim 1 as follows:

1. (Amended) A process for producing compound semiconductor single crystal, comprising the steps of:
- a) placing a compound semiconductor raw material into a crucible;
- b) encapsulating the raw material;

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